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Buffer layer-less fabrication of high-mobility transparent oxide semiconductor, La-doped BaSnO₃

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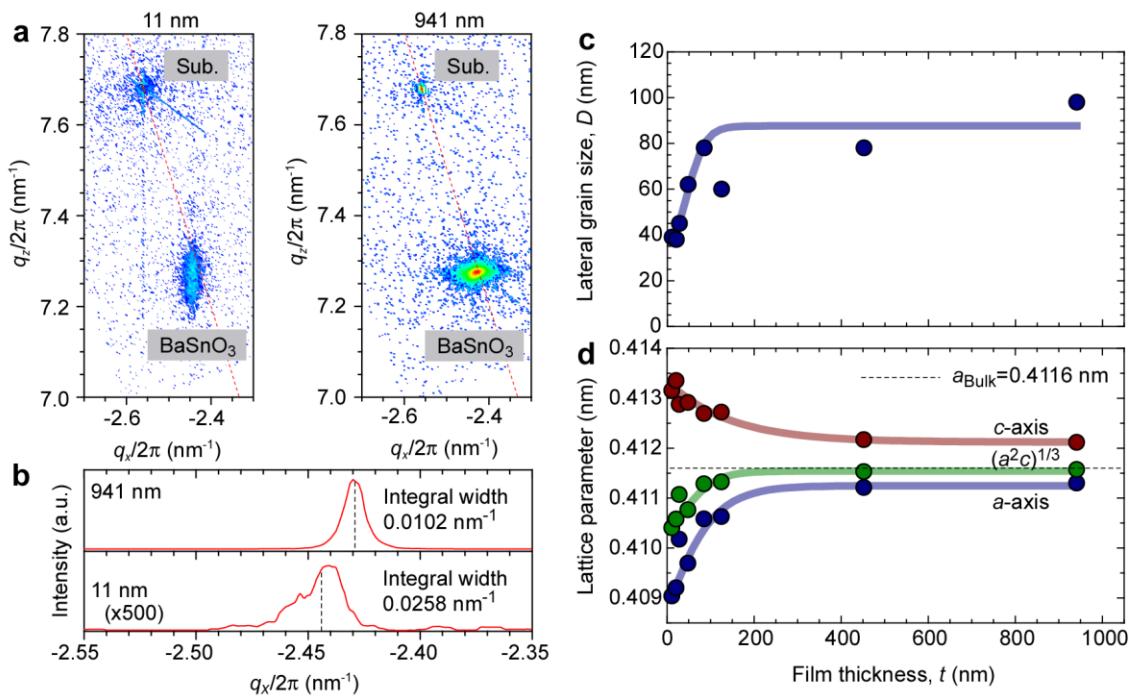


Figure S1. Crystallographic characterizations of the O₃-La_{0.02}-Ba_{0.98}SnO₃ films grown on (001) SrTiO₃ substrates. (a) reciprocal space mappings of asymmetric (103) diffraction of O₃-LBSO films. The symmetry axis of a cubic lattice is indicated by a red line. (103) BaSnO₃ diffraction peak approaches the red line, which suggests that lattice strain due to the film/substrate mismatch is gradually decreasing; (b) the cross-sectional intensity plot along the in-plane axis in reciprocal space ($q_x/2\pi$); (c) thickness dependence of the lateral grain sizes; (d) thickness dependent lattice parameter along the in-plane direction (blue), out-of-plane direction (red), and the average lattice parameter (green). All these values approach the lattice parameter of bulk LBSO (black dashed line) with increasing film thickness.

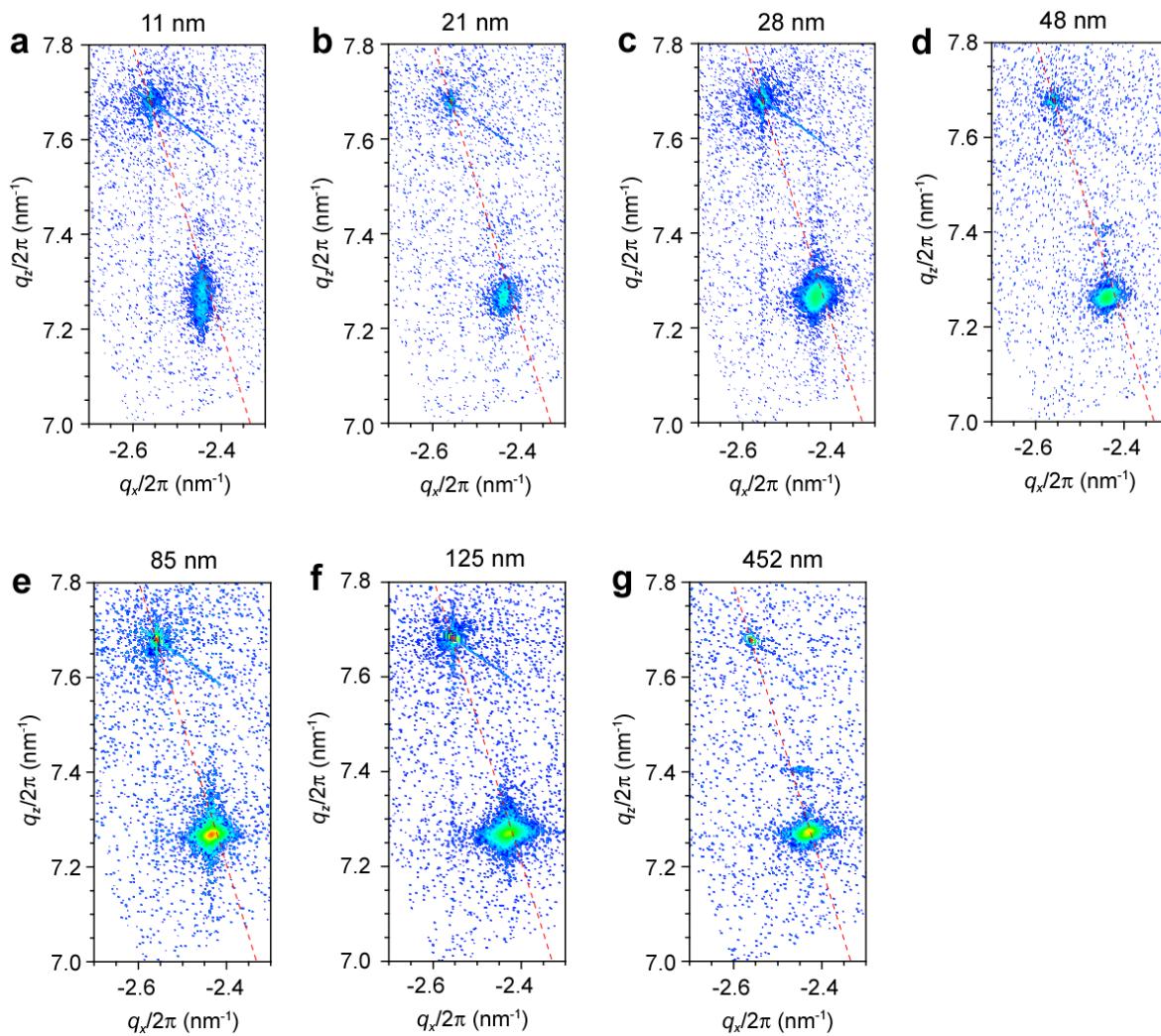


Figure S2. Reciprocal space mappings of $\text{O}_3\text{-La}_{0.02}\text{-Ba}_{0.98}\text{SnO}_3$ films grown on (001) SrTiO_3 substrate around the (103) Bragg diffraction. The thicknesses of the films were (a) 11 nm, (b) 21 nm, (c) 28 nm, (d) 48 nm, (e) 85 nm, (f) 125 nm and (g) 452 nm. Although very weak diffraction spot is seen at $(q_x, q_z) = (-2.45, 7.4)$ in g, probably due to the formation of Ruddlesden-Popper type faults, overall crystal phase of the films is BaSnO_3 .

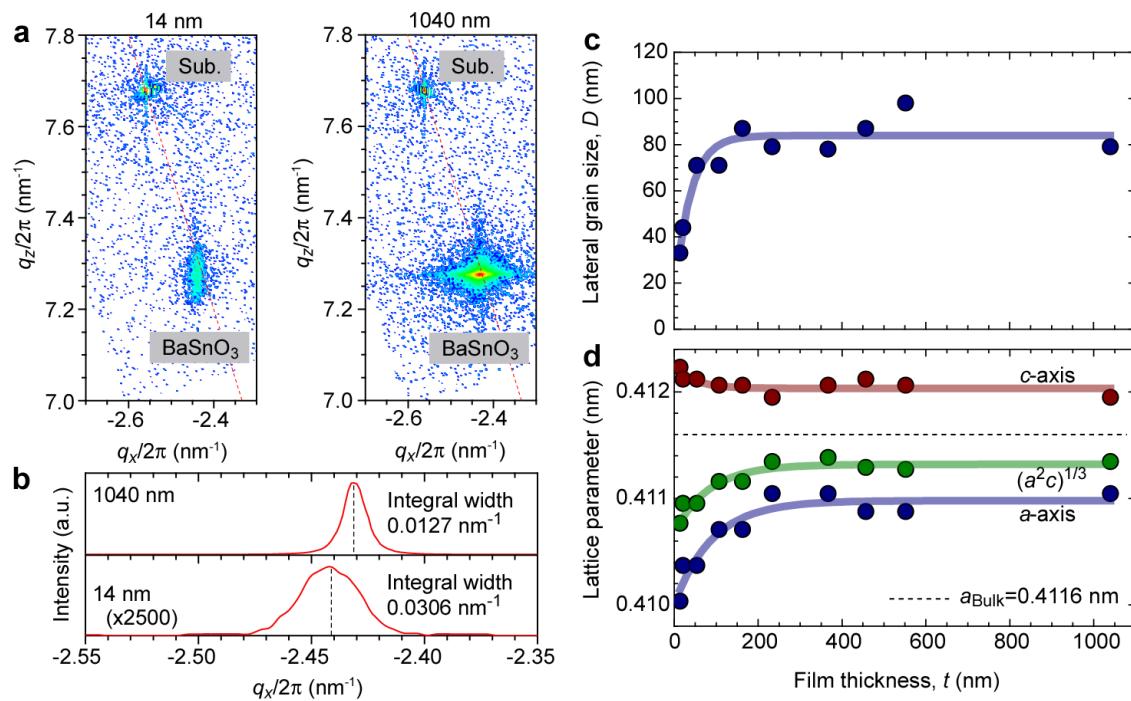


Figure S3. Crystallographic characterizations of the O₂-La_{0.02}-Ba_{0.98}SnO₃ films grown on (001) SrTiO₃ substrates.²³ (a) reciprocal space mappings of asymmetric (103) reflection of O₃-LBSO films. The symmetry axis of a cubic lattice is indicated by a red line. (103) BaSnO₃ diffraction peak approaches the red line, which suggests that lattice strain due to the film/substrate mismatch is gradually decreasing; (b) the cross-sectional intensity plot along the in-plane axis in reciprocal space ($q_x/2\pi$); (c) thickness dependence of the lateral grain sizes; (d) thickness dependent lattice parameter along the in-plane direction (blue), out-of-plane direction (red), and the average lattice parameter (green). All these values approach the lattice parameter of bulk LBSO (black dashed line) with increasing film thickness. The crystallographic characteristics of O₂-LBSO films were very similar with those of O₃-LBSO films.

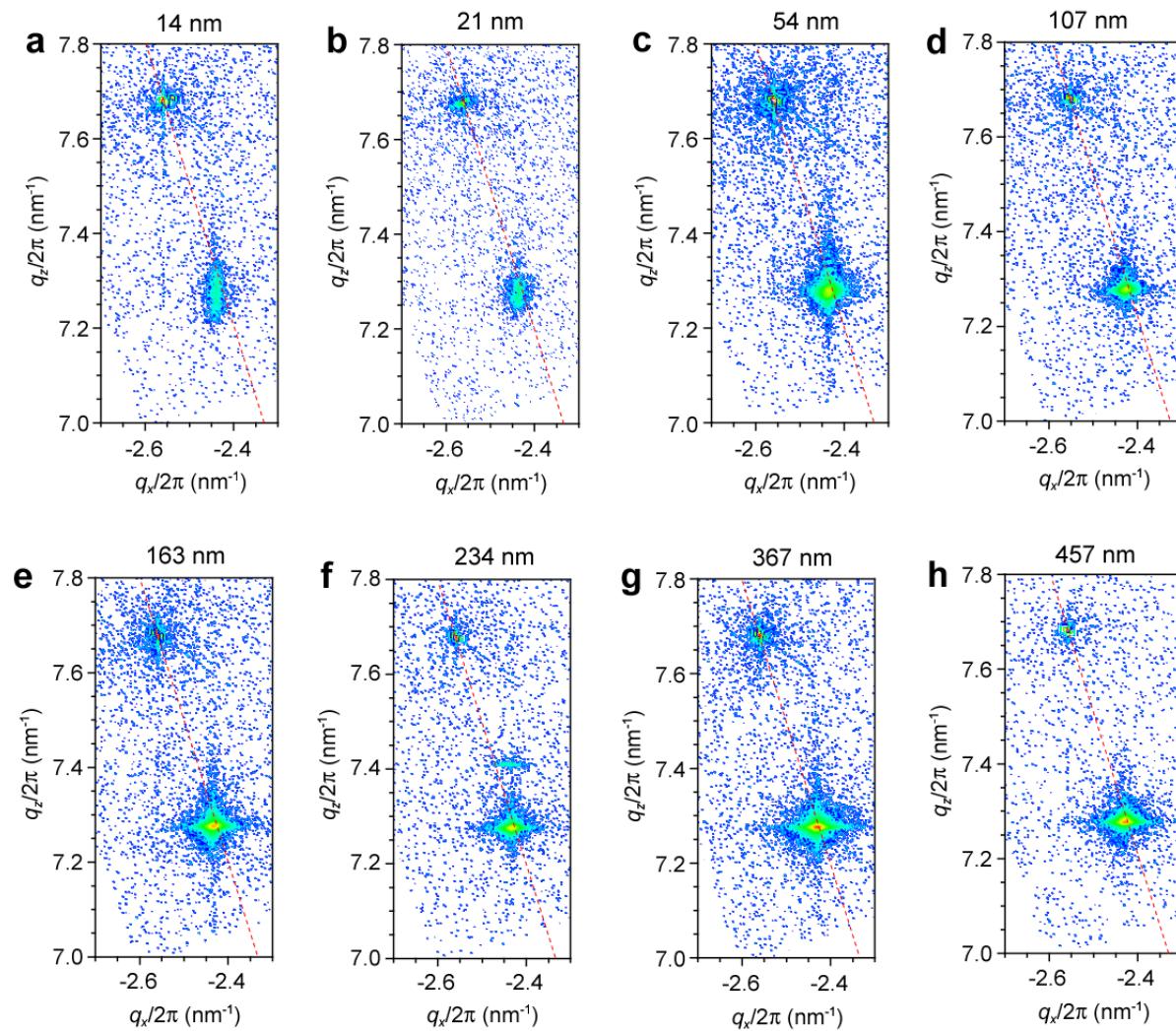


Figure S4. Reciprocal space mappings of O_2 -La_{0.02}-Ba_{0.98}SnO₃ films grown on (001) SrTiO₃ substrates around the (103) Bragg diffraction.²³ The thicknesses of the films were (a) 14 nm, (b) 21 nm, (c) 54 nm, (d) 107 nm, (e) 163 nm, (f) 234 nm, (g) 367 nm, and (h) 457 nm. Although very weak diffraction spot is seen at $(q_x, q_z) = (-2.45, 7.4)$ in f, probably due to the formation of Ruddlesden-Popper type faults, overall crystal phase of the films is BaSnO₃.

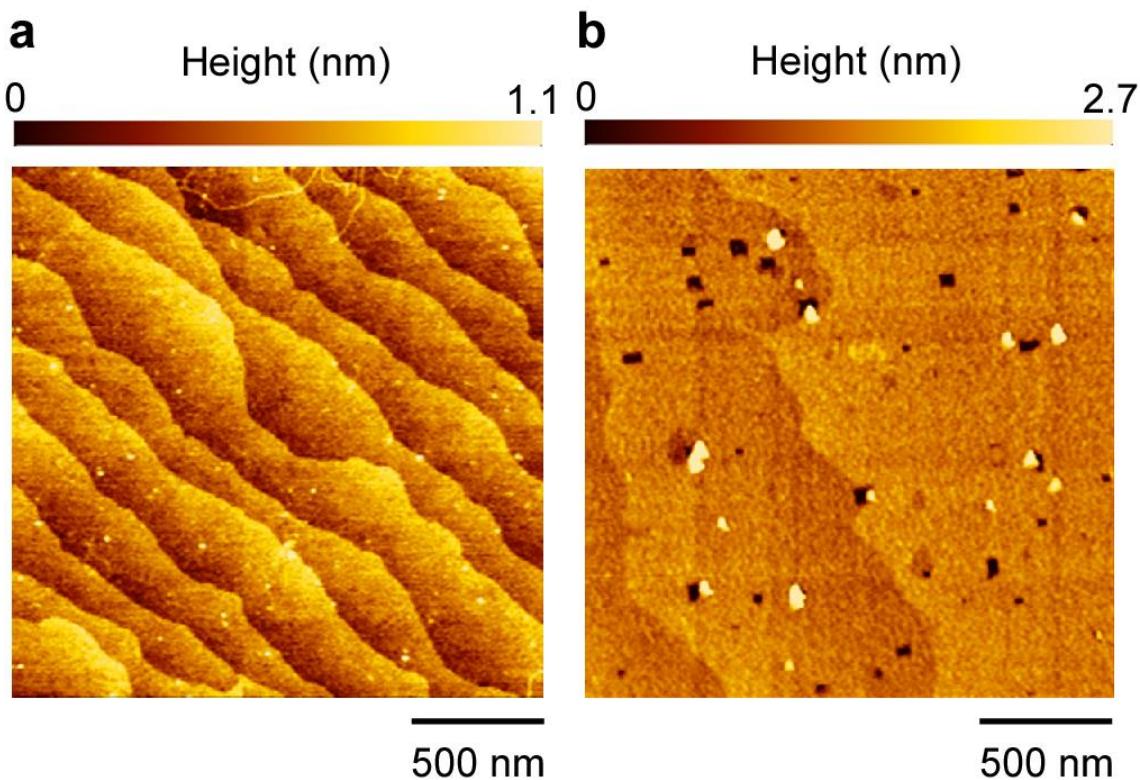


Figure S5. Topographic AFM images of the $\text{La}_{0.02}\text{-Ba}_{0.98}\text{SnO}_3$ films. (a) O_2 -LBSO and (b) O_3 -LBSO. Stepped and terrace structures were observed in both cases, which are commonly observed in high-quality epitaxial films. The oxygen conditions during the film growth do not seem to affect the film surface of the films.